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DL4454

Silicon Switching Diode 500 mW 75 Volt

Features

- Fast Switching Speed
- Low Current Leakage
- Low Cost
- Compression Bond Construction
- Surface Mount Application

Maximum Ratings

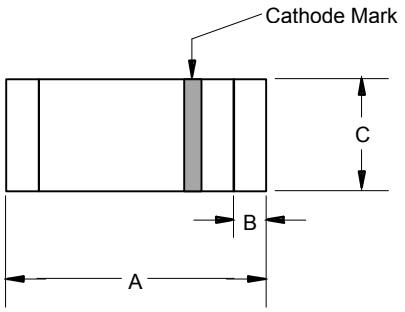
- Operation & Storage Temperature: -55°C to +150°C
- Maximum Thermal Resistance: 400K/W Junction to Ambient

Electrical Characteristics @ 25°C Unless Otherwise Specified

Reverse Volt.	V_R	50V	
Peak Reverse Volt.	V_{RM}	75V	
Average Rectified Current	I_O	150mA	Resistive Load f>50Hz
Power Dissipation	P_{TOT}	500mW	
Junction Temperature	T_J	175°C	
Peak Forward Surge Current	I_{FSM}	500mA	8.3ms, half sine
Maximum Instantaneous Forward Volt.	V_F	1.0V	I_{FM}=10mA; T_J=25°C
Maximum DC Reverse Current At Rated DC Blocking Volt.	I_R	0.1uA	V_R=50V T_J=25°C
Typical Junction Capacitance	C_J	2pF	Measured at 1.0MHz, V_R=4.0V
Reverse Recovery Time	T_{rr}	4nS	I_F=10mA V_R=6V I_R=1mA R_L=100OHMS

Pulse test: Pulse width 300 usec, Duty cycle 2%.

MINIMELF



DIMENSION					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.134	.142	3.40	3.60	
B	.008	.016	0.20	0.40	
C	.055	.059	1.40	1.50	

SUGGESTED SOLDER PAD LAYOUT

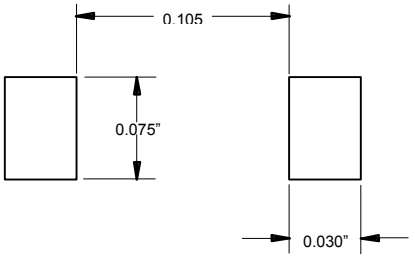
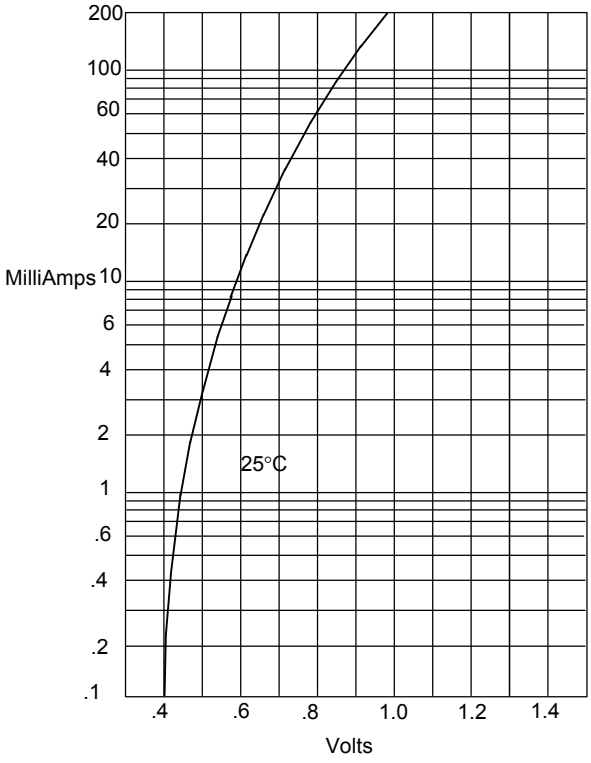
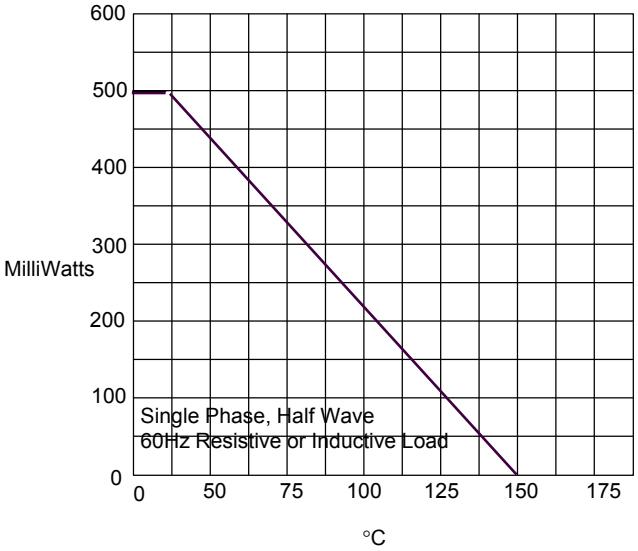


Figure 1
Typical Forward Characteristics



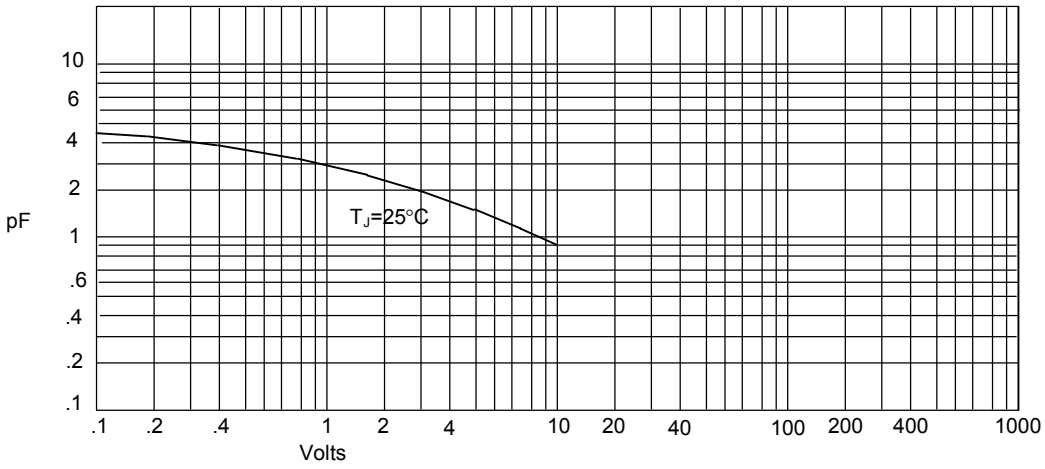
Instantaneous Forward Current - Amperes *versus*
Instantaneous Forward Voltage - Volts

Figure 2
Forward Derating Curve



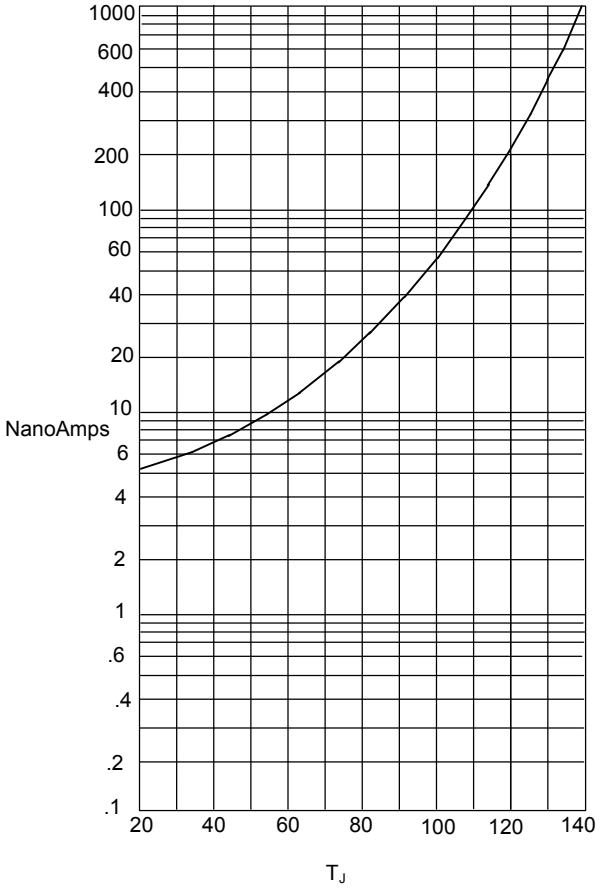
Admissable Power Dissipation - MilliWatts *versus*
Ambient Temperature -°C

Figure 3
Junction Capacitance



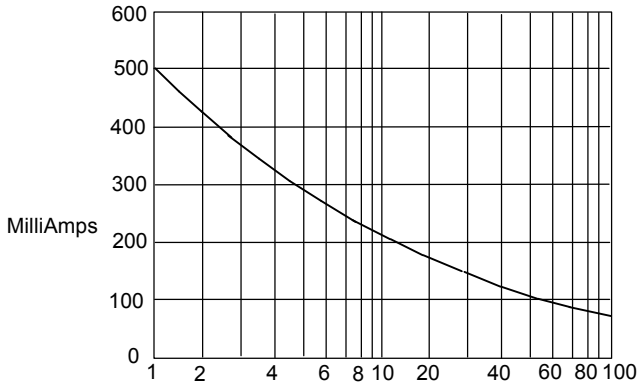
Junction Capacitance - pF *versus*
Reverse Voltage - Volts

Figure 4
Typical Reverse Characteristics



Instantaneous Reverse Leakage Current - NanoAmperes *versus*
Junction Temperature -°C

Figure 5
Peak Forward Surge Current



Peak Forward Surge Current - Amperes *versus*
Number Of Cycles At 60Hz - Cycles